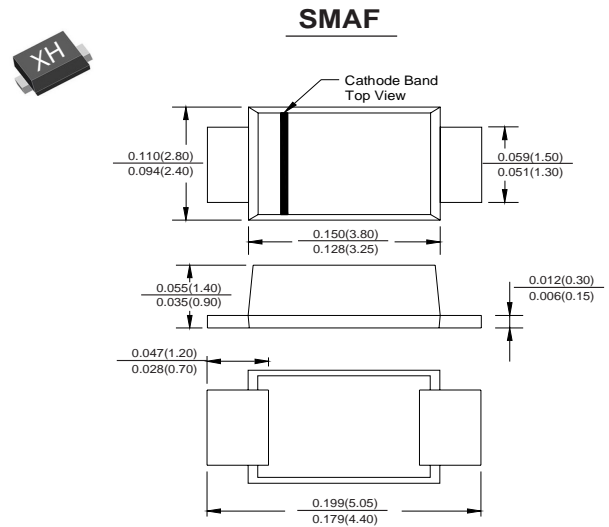


FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Superfast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/EU directives

MECHANICAL DATA

- Case: SMAF
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 27mg 0.00086oz



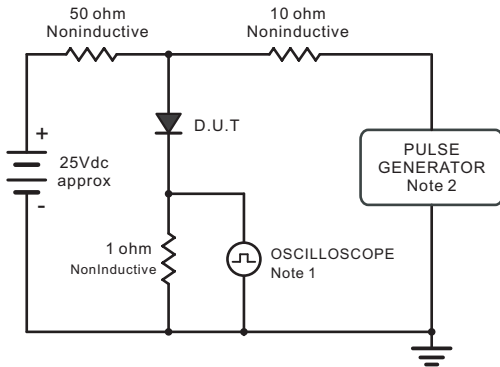
Dimensions in inches and (millimeters)

Absolute Maximum Ratings and Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Symbols	ES3AF	ES3BF	ES3CF	ES3DF	ES3EF	ES3GF	ES3JF	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	600	V
Maximum RMS voltage	V_{RMS}	35	70	105	140	210	280	420	V
Maximum DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	600	V
Maximum Average Forward Rectified Current at $T_L = 100\text{ }^\circ\text{C}$	$I_{F(AV)}$	3							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	100							A
Maximum Forward Voltage at 3A	V_F	1			1.25		1.7		V
Maximum DC Reverse Current at Rated DC Blocking Voltage $T_a = 25\text{ }^\circ\text{C}$ $T_a = 125\text{ }^\circ\text{C}$	I_R	5 200							μA
Typical Junction Capacitance at $V_R = 4\text{V}$, $f = 1\text{MHz}$	C_j	45							pF
Maximum Reverse Recovery Time at $I_F = 0.5\text{A}$, $I_R = 1\text{A}$, $I_{rr} = 0.25\text{A}$	t_{rr}	35							ns
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150							$^\circ\text{C}$

Fig.1 Reverse Recovery Time Characteristic And Test Circuit Diagram



Note: 1. Rise Time = 7ns, max.
 Input Impedance = 1megohm, 22pF.
 2. Rise Time = 10ns, max.
 Source Impedance = 50 ohms.

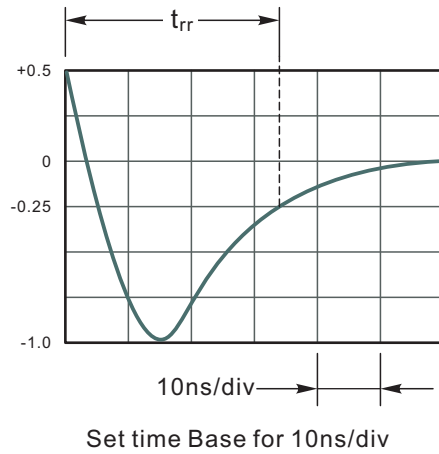


Fig.2 Maximum Average Forward Current Rating

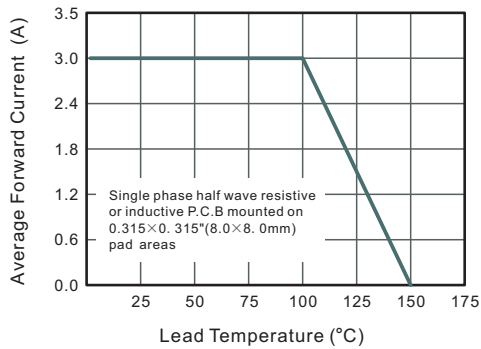


Fig.3 Typical Reverse Characteristics

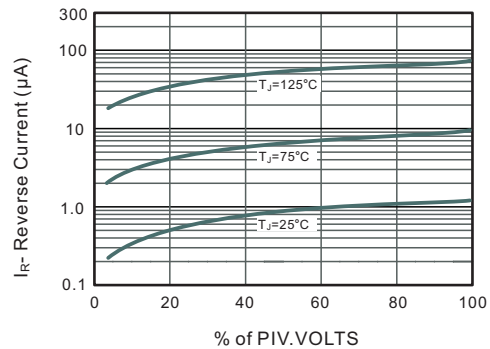


Fig.4 Typical Forward Characteristics

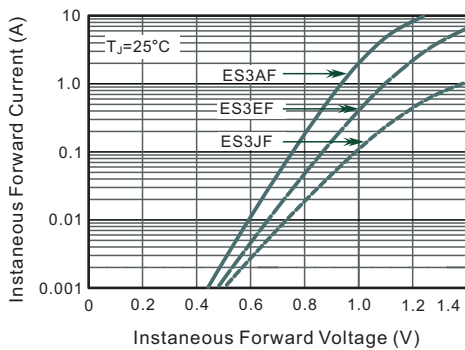


Fig.5 Typical Junction Capacitance

